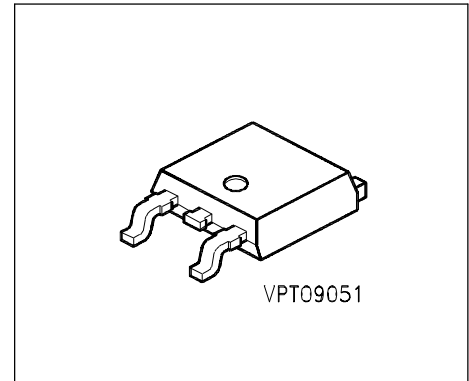


**IGBT**

- Low forward voltage drop
- High switching speed
- Low tail current
- Latch-up free
- Avalanche rated



<b>Pin 1</b>	<b>Pin 2</b>	<b>Pin 3</b>
G	C	E

Type	$V_{CE}$	$I_C$	Package	Ordering Code
SGD02N60	600V	2A	P-TO252	Q67040-A . . . .

**Maximum Ratings**

Parameter	Symbol	Values	Unit
Collector-emitter voltage	$V_{CE}$	600	V
Collector-gate voltage	$V_{CGR}$	600	
$R_{GE} = 20 \text{ k}\Omega$			
Gate-emitter voltage	$V_{GE}$	$\pm 20$	
DC collector current	$I_C$		A
$T_C = 25 \text{ }^\circ\text{C}$		5.5	
$T_C = 100 \text{ }^\circ\text{C}$		2	
Pulsed collector current, $t_p = 1 \text{ ms}$	$I_{Cpuls}$		
$T_C = 25 \text{ }^\circ\text{C}$		11	
$T_C = 100 \text{ }^\circ\text{C}$		4	
Avalanche energy, single pulse	$E_{AS}$		mJ
$I_C = 2 \text{ A}$ , $V_{CC} = 50 \text{ V}$ , $R_{GE} = 25 \text{ }\Omega$		3	
$L = 1.5 \text{ mH}$ , $T_j = 25 \text{ }^\circ\text{C}$			
Power dissipation	$P_{tot}$		W
$T_C = 25 \text{ }^\circ\text{C}$		30	

## Preliminary data

### Maximum Ratings

Parameter	Symbol	Values	Unit
Chip or operating temperature	$T_j$	-55 ... + 150	°C
Storage temperature	$T_{stg}$	-55 ... + 150	
IEC climatic category, DIN IEC 68-1	-	55 / 150 / 56	-

### Thermal Characteristics

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance , junction - case	$R_{thJC}$	-	-	4.2	K/W
Thermal resistance, junction - ambient ( PCB mount)**	$R_{thJA}$	-	50	-	

\*\* Device on 50mm x 50 mm x 1.5 mm epoxy PCB ( FR-4 ) with 6 cm<sup>2</sup> copper area around the heat slug footprint ( one layer, 70 μm copper ).  
PCB is vertical without blown air.

### Electrical Characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

### Static Characteristics

Collector-emitter breakdown voltage $V_{GE} = 0\text{ V}$ , $I_C = 0.5\text{ mA}$ , $T_j = -55\text{ °C}$	$V_{(BR)CES}$	600	-	-	V
Gate threshold voltage $V_{GE} = V_{CE}$ , $I_C = 0.15\text{ mA}$ , $T_j = 25\text{ °C}$ $V_{GE} = V_{CE}$ , $I_C = 0.15\text{ mA}$ , $T_j = 150\text{ °C}$	$V_{GE(th)}$	3 2	4 3	5 -	
Collector-emitter saturation voltage $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$ , $T_j = 25\text{ °C}$ $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$ , $T_j = 150\text{ °C}$	$V_{CE(sat)}$	1.6 -	2 2.3	2.5 2.8	
Zero gate voltage collector current $V_{CE} = 600\text{ V}$ , $V_{GE} = 0\text{ V}$ , $T_j = 25\text{ °C}$ $V_{CE} = 600\text{ V}$ , $V_{GE} = 0\text{ V}$ , $T_j = 150\text{ °C}$	$I_{CES}$	- -	- -	20 250	μA
Gate-emitter leakage current $V_{GE} = 25\text{ V}$ , $V_{CE} = 0\text{ V}$	$I_{GES}$	-	-	100	

*Preliminary data*

Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**AC Characteristics**

Transconductance $V_{CE} = 20\text{ V}, I_C = 2\text{ A}$	$g_{fs}$	0.45	1.6	-	S
Input capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{iss}$	-	150	190	pF
Output capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{oss}$	-	20	25	
Reverse transfer capacitance $V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	$C_{rss}$	-	10	13	

**Preliminary data**
**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Switching Characteristics, Inductive Load at  $T_j = 150\text{ °C}$** 

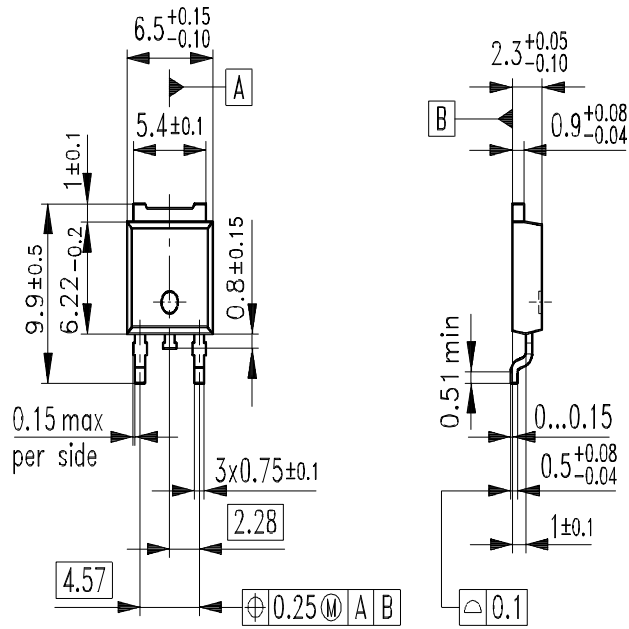
Turn-on delay time $V_{CC} = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$ $R_{Gon} = 118\ \Omega$	$t_{d(on)}$	-	20	30	ns
Rise time $V_{CC} = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$ $R_{Gon} = 118\ \Omega$	$t_r$	-	15	23	
Turn-off delay time $V_{CC} = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$ $R_{Goff} = 118\ \Omega$	$t_{d(off)}$	-	280	420	
Fall time $V_{CC} = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$ $R_{Goff} = 118\ \Omega$	$t_f$	-	110	165	
Total turn-on loss energy * $V_{CC} = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$ $R_{Gon} = 118\ \Omega$ , $T_j = 150\text{ °C}$	$E_{on}$	-	0.12	0.16	mJ
Total turn-off loss energy $V_{CC} = 400\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$ $R_{Goff} = 118\ \Omega$ , $T_j = 150\text{ °C}$	$E_{off}$	-	0.05	0.065	
Total Gate Charge $V_{CC} = 480\text{ V}$ , $V_{GE} = 15\text{ V}$ , $I_C = 2\text{ A}$	$Q_{G(on)}$	-	14	21	nC

\* includes the reverse recovery losses caused by the FWD of the BUP410D

**Package Outlines**

Dimensions in mm

Weight:



GPT09051

All metal surfaces tin plated, except area of cut.